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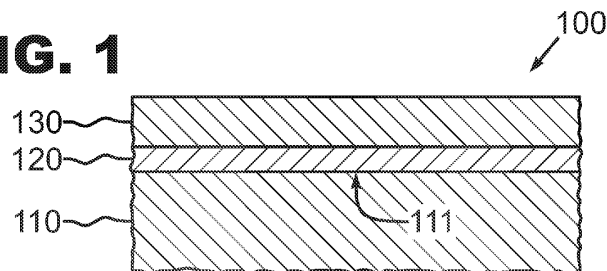
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(54) Title: SEMICONDUCTOR STRUCTURE AND METHOD

FIG. 1



(57) Abstract: This disclosure relates to a semiconductor structure (100), comprising a crystalline silicon substrate (110), having a surface (111), and a crystalline silicon oxide superstructure (120) on the surface (111) of the silicon substrate (110), the silicon oxide superstructure (120) having a thickness of at least two molecular layers and a (1 x 1) plane structure using Wood's notation.10.